

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant:	Hattangady et al.	Art Unit:	TBD
Serial No.:	TBD	Examiner:	TBD
Filing Date:	02/19/2004	Docket No.:	TI-31017.1
Customer No.:	23494	Conf. No.:	TBD
Title:	SEMICONDUCTOR WITH A NITRIDED SILICON GATE OXIDE AND METHOD		

**PRELIMINARY AMENDMENT**

Commissioner of Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Prior to the review of the above subject patent application, please make the following amendments:

In the Specification:

Please amend the specification by inserting before the first line the sentence:

--This is a divisional application of Serial No. 10/326,188 filed 12/20/2002.

*now U.S. Patent 6,716,695*

In the Claims:

Please cancel Claims 1-15.

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